(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
28 April 2005 (28.04.2005)

PCT

(10) International Publication Number
WO 2005/038892 A1

(51) International Patent Classification[7]: H01L 21/302, 21/461

(21) International Application Number: PCT/US2004/032793

(22) International Filing Date: 5 October 2004 (05.10.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/680,895 8 October 2003 (08.10.2003) US

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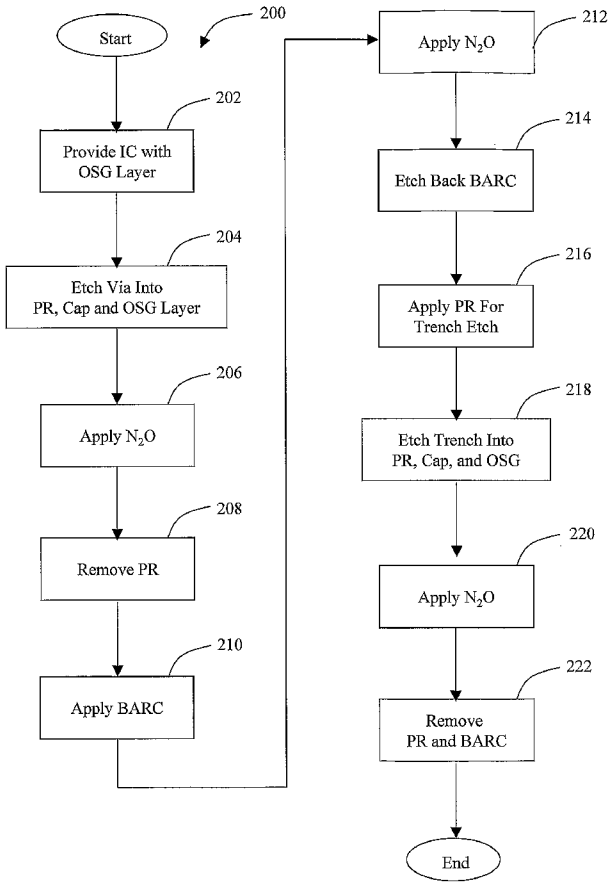
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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,

[Continued on next page]

(54) Title: A NITROUS OXIDE STRIPPING PROCESS FOR ORGANOSILICATE GLASS



(57) Abstract: A method of stripping an integrated circuit (IC) structure having a photoresist material and an organosilicate glass (OSG) material is described. The method comprises feeding a nitrous oxide (N2O) gas into a reactor, generating a plasma in the reactor and stripping the photoresist. The stripping process provides a high selectivity between the photoresist and the OSG material.

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ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report*

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

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